

A Warm Welcome to A New T-ED Editor

I AM DELIGHTED to announce the appointment to the T-ED Editorial Board of Dr. Ravi Todi of Qualcomm, San Diego, CA, in the area of MOS Devices and Technology.

Ravi is a recognized expert in this arena, and a fine addition to the T-ED Editorial Board. A short biography of his accomplishments is given below. Welcome aboard!

JOHN D. CRESSLER, *Editor-in-Chief*
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Ravi Todi received the M.S. degrees in electrical and mechanical engineering from the University of Central Florida, Orlando, FL, USA, and the Ph.D. degree in electrical engineering, in 2004, 2005, and 2007, respectively.

His graduate research work focused on gate-stack engineering, with emphasis on binary metal alloys as gate electrode and on high-mobility Ge-channel devices. In 2007, he was an Advisory Engineer/Scientist at Semiconductor Research and Development Center, IBM Microelectronics Division, Essex Junction, VT, USA, where he was involved in high-performance eDRAM integration on 45-nm SOI logic platform. In 2010, he was the Lead Engineer for 22-nm SOI eDRAM development. He joined Qualcomm, Inc., San Diego, CA, USA, in 2012, responsible for 20-nm technology and product development as part of Qualcomm's foundry engineering team. He is also responsible for early learning on 16/14-nm FinFET technology nodes. He has authored and co-authored over 50 publications, has several issues U.S. patents and over 25 pending disclosures.

Dr. Todi was a recipient of IBM's Outstanding Technical Achievement Award in 2011 for his many contributions to the success of eDRAM program at IBM, Armonk, NY, USA.